

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC2240

Low Noise Audio Amplifier Applications

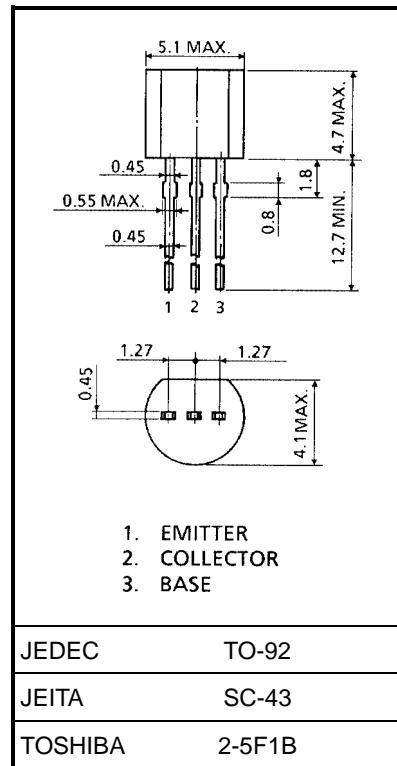
Unit: mm

The 2SC2240 is a transistor for low frequency and low noise applications. This device is designed to lower noise figure in the region of low signal source impedance, and to lower the pulse noise. This is recommended for the first stages of Equalizer amplifiers.

- Low noise: NF = 4dB (typ.) RG = 100 Ω, V_{CE} = 6 V, I_C = 100 μA,
f = 1 kHz
: NF = 0.5dB (typ.) RG = 1 kΩ, V_{CE} = 6 V, I_C = 100 μA,
f = 1 kHz
- Low pulse noise: Low 1/f noise
- High DC current gain: h_{FE} = 200~700
- High breakdown voltage: V_{CEO} = 120 V

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	120	V
Collector-emitter voltage	V _{CEO}	120	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA
Base current	I _B	20	mA
Collector power dissipation	P _C	300	mW
Junction temperature	T _j	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 0.21 g (typ.)

Electrical Characteristics ($T_a = 25^\circ C$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 120 V, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 V, I_C = 0$	—	—	0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$	120	—	—	V
DC current gain	h_{FE} (Note)	$V_{CE} = 6 V, I_C = 2 mA$	200	—	700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 mA, I_B = 1 mA$	—	—	0.3	V
Base-emitter voltage	V_{BE}	$V_{CE} = 6 V, I_C = 2 mA$	—	0.65	—	V
Transition frequency	f_T	$V_{CE} = 6 V, I_C = 1 mA$	—	100	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$	—	3.0	—	pF
Noise figure	NF	$V_{CE} = 6 V, I_C = 0.1 mA, f = 10 Hz, R_G = 10 k\Omega$	—	—	6	dB
		$V_{CE} = 6 V, I_C = 0.1 mA, f = 1 kHz, R_G = 10 k\Omega$	—	—	2	
		$V_{CE} = 6 V, I_C = 0.1 mA, f = 1 kHz, R_G = 100 \Omega$	—	4	—	

Note: h_{FE} classification GR: 200~400, BL: 350~700